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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/484,348	01/18/2000	Stanley E. Swirhun	36903/SAH/C715	9594
3017	7590 08/12/2003			
BARLOW, JOSEPHS & HOLMES, LTD. 101 DYER STREET 5TH FLOOR			EXAMINER	
			LOUIE, WAI SING	
PROVIDENC	E, RI . 02903		ART UNIT	PAPER NUMBER
			2814	
			DATE MAILED: 08/12/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

		4/C					
,	Application No.	Applicant(s)					
Office Action Summer	09/484,348	SWIRHUN ET AL.					
Office Action Summary	Examiner	Art Unit					
The MAILING DATE of this communication	Wai-Sing Louie	2814					
Th MAILING DATE of this communication apperent of the second for Reply	ears on the cover sheet with the c	correspondenc address					
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply if NO period for reply is specified above, the maximum statutory period with Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	6(a). In no event, however, may a reply be tir within the statutory minimum of thirty (30) day ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. 8 133)					
1)⊠ Responsive to communication(s) filed on <u>11 Ju</u>	uly 2003 .						
2a)☐ This action is FINAL . 2b)⊠ This	s action is non-final.						
3) Since this application is in condition for alloward closed in accordance with the practice under EDisposition of Claims	nce except for formal matters, p Ex parte Quayle, 1935 C.D. 11, 4	rosecution as to the merits is 153 O.G. 213.					
4) ☐ Claim(s) 22-35 is/are pending in the application							
	4a) Of the above claim(s) is/are withdrawn from consideration.						
	.						
6)⊠ Claim(s) <u>22-35</u> is/are rejected.							
7) Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction and/or	election requirement.						
Application Papers							
9)☐ The specification is objected to by the Examiner.							
10)☐ The drawing(s) filed on is/are: a)☐ accept	ed or b)⊡ objected to by the Exa	miner.					
Applicant may not request that any objection to the							
11) The proposed drawing correction filed on		ved by the Examiner.					
If approved, corrected drawings are required in repl							
12) The oath or declaration is objected to by the Exa	miner.						
Priority under 35 U.S.C. §§ 119 and 120							
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).							
a) ☐ All b) ☐ Some * c) ☐ None of:							
1. ☐ Certified copies of the priority documents have been received.							
2. Certified copies of the priority documents have been received in Application No							
3. ☐ Copies of the certified copies of the priorit application from the International Bure * See the attached detailed Office action for a list of the control of the priority application.	au (PCT Rule 17.2(a)).	-					
14) Acknowledgment is made of a claim for domestic							
 a) ☐ The translation of the foreign language provides 15)☐ Acknowledgment is made of a claim for domestic 	isional application has been rece	eived.					
Attachment(s)							
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal P	(PTO-413) Paper No(s) atent Application (PTO-152)					
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DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 22-26, 28-29, 32, and 34-35 are rejected under 35 U.S.C. 103(a) as being unpatentable over Olbright et al. (US 5,266,794).

With regard to claim 22, Olbright et al. disclose an integrated light emitting device and photo detector (col. 3, line 48 to col. 9, line 39 and fig. 9) comprising:

- A semiconductor substrate 200 (fig. 8);
- An optical transmitter 180 formed on a portion of the substrate 200 (fig. 8);
- An optical receiver 190 formed on the substrate 200 laterally adjacent the optical transmitter 180, the optical receiver 190 optically isolated from the optical transmitter 180 (fig 8). Since the optical receiver 190 and the optical transmitter 180 are formed on an intrinsic GaAs substrate (fig. 8), therefore, it would have been obvious that the optical receiver 190 is electrically isolated from the optical transmitter 180.

With regard to claim 23, Olbright et al. disclose the optical receiver comprises a photodiode (col. 7, line 60).

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With regard to claim 24, Olbright et al. disclose the optical transmitter comprises a VCSEL having a plurality of layers (fig. 8).

With regard to claim 25, Olbright et al. disclose the VCSEL comprises an isolation region defining discrete areas of the active VCSEL layers and the inactive VCSEL layers (fig. 8).

With regard to claims 26 and 32, Olbright et al. disclose the means for disabling inactive VCSEL layers is by electronically disabling the associated transmitters (col. 4, lines 20-24).

With regard to claim 28, Olbright et al. disclose the active region comprises a multiple quantum well layer (col. 8, line 14).

With regard to claim 29, Olbright et al. disclose the first and second mirrors are epitaxially grown distributed Bragg reflector layers (col. 8, line 13).

With regard to claim 34, Olbright et al. disclose a photodiodes formed on the semiconductor substrate (fig. 8).

With regard to claim 35, Olbright et al. disclose a monolithically integrated optical device having a VCSEL and an optical receiver. The receiver can comprise a metal-semiconductor-metal photodiode (Olbright col. 7, lines 59-61).

Claims 30-31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Olbright et al. (US 5,266,794) in view of Hasnain et al. (US 5,136,603).

With regard to claim 30, Olbright et al. do not disclose a photodiode formed on a top most second mirror layer of the VCSEL layers. However, Hasnain et al. disclose forming a PIN photodiode formed on a top most second mirror layer of the VCSEL layers (Hasnain fig. 1). Hasnain et al. teach the photodiode is integrated with the VCSEL becomes a single mode

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operation and have low divergence optical output (Hasnain col. 1, lines 45-53). Therefore, it would have been obvious to one with ordinary skill in the art to modify Olbright's device with the teaching of Hasnain et al. to place the photodiode on the top most second mirror layer in order to operate the device as a single mode and have low divergence optical output.

With regard to claim 31, Olbright et al. disclose optical receiver comprises:

- A p-type layer 220a formed on a portion of the VCSEL layers (fig. 8);
- An n-type layer 230a (fig. 8);
- A photodiode cathode contact 330 formed on the n-type layer (fig. 8);
- Olbright et al. do not disclose an intrinsic layer. However, one with ordinary skill
 in the art would know a PN photodiode could be replaced by a PIN photodiode to
 improve the confinement of the carriers, such as the device disclosed by Hasnain
 et al., which has a PIN photodiode on top of the VCSEL. Therefore, it would have
 been obvious to have a PIN diode and having an intrinsic layer on top of the ptype layer 220a;
- A photodiode anode 320 formed on the p-type layer 220a (fig. 8). Although, the
 contact is not made on the top most second mirror layer, but the contact is made
 on a p-layer of the PIN photo detector to complete the circuit and, therefore, is
 considered as equivalent.

Claims 27 and 33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Olbright et al. (US 5,266,794) in view of Lebby et al. (US 5,498,883).

With regard to claim 27, Olbright et al. disclose the optical transmitter comprises:

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• A first mirror layers 270 formed on the substrate (fig. 8);

- An active region 250 formed on said first cladding layer (fig. 8);
- A second mirror 260 formed on said second cladding layer (fig. 8);
- Olbright et al. do not disclose a first and a second cladding layer formed on a top
 and beneath the active layer. However, cladding layers are used in VCSEL to
 improve the confinement of the carriers, which is common in the art, such as
 disclose in Lebby et al. (Lebby col. 3, lines 24-43 and fig. 3). Therefore, it would
 have been obvious have cladding layers surrounding the active region.

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With regard to claim 33, Olbright et al. do not disclose using a non-reflective coating. However, Lebby et al. disclose an anti-reflective coating is used in the device (fig. 3). Lebby et al. teach the anti-reflective coating suppresses lasing (Lebby col. 5, lines 27-30). Therefore, it would have been obvious to one with ordinary skill in the art to apply anti-reflective coating on the device. Doing so could control the light by suppress lasing.

Response to Arguments

Applicant's arguments filed 7/11/03 have been fully considered:

• Applicant argues that the optical transmitter and the optical receiver in Olbright et al. work in interlocked relation by communication through the substrate and in particular by communication through the semiconductor substrate having logic etched thereon (page 7). However, the substrate in Olbright's device is an intrinsic GaAs substrate (fig. 8), which is not a conductor. Therefore, the optical transmitter and optical receiver are isolated. There is nothing in the present claim

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to prevent the optical transmitter and the optical receiver from communication (cross talk) with each other through other means. Olbright et al. meet all limitations in claim 22.

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- Applicant argues that there is no teaching either alone or in combination of these cited references (Olbright et al. and Hasnain et al.) that provides for the placement in close proximity of photodiode and VCSEL portion of the module through the use of a proton injected isolation region. However, Hasnain et al. utilize the upper p-type DBR mirror as the p-layer of the pin-junction and build the rest of the pin-junction structure on top of the p-type DBR mirror. Hasnain et al. teach the photodiode is integrated with the VCSEL becomes a single mode operation and have low divergence optical output (Hasnain col. 1, lines 45-53). This meets the claim limitations of claim 30-31 and the combination is proper.
- Applicant argues that the combination of Olbright et al. and Lebby et al. is improper and do not disclose the specific isolation limitations that restrict both electrical and optical interference. Examiner stated in the office action that cladding layers are used in VCSEL to improve the confinement of the carriers, which is common in the art. Lebby's device includes cladding layers around the active region. There are numerous references having cladding layers around an active region. Therefore, the combination is proper. In claims 27 and 33, there are no limitations on restrict both electrical and optical interference. The argument is moot.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wai-Sing Louie whose telephone number is (703) 305-0474. The examiner can normally be reached on 7:30 AM to 4:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is/(793) 308-0956.

LONG PHAM
PRIMARY EXAMINER

wsl

August 4, 2003